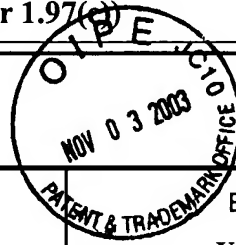


TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
SETI-0006

In Re Application Of: Fareed et al.



Serial No.
10/659,183

Filing Date
September 10, 2003

Examiner
Unknown

Group Art Unit
Unknown

Title: **HETEROSTRUCTURE SEMICONDUCTOR DEVICE**

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

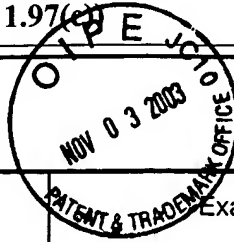
37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
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HETEROSTRUCTURE SEMICONDUCTOR DEVICE

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. 500999 as described below.
- ☐ Charge the amount of _____
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Signature of Person Mailing Correspondence

Dorothea Rubbone

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Dated: October 30, 2003

John W. LaBatt

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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

SETI-0006

Application Number

10/659,183

Applicant(s)

Fareed et al.

Filing Date

September 10, 2003

Group Art Unit

Unknown

*EXAMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version).

"High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, Charlottesville, VA, December 1997, pp. 377-380.

"Optoelectronic GaN-Based Field Effect Transistors," M. S. Shur et al., SPIE Vol. 2397, pp. 294-303.

"Current/Voltage Characteristic Collapse in AlGaIn/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2175-2176.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.